

# GD2X30MPS12D

## 1200V 60A SiC Schottky MPS™ Diode



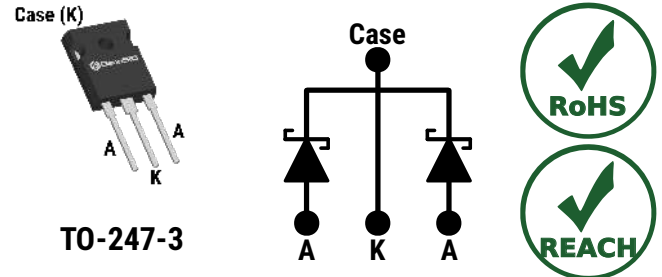
### Silicon Carbide Schottky Diode

$V_{RRM}$	=	1200 V
$I_F(T_C = 148^\circ\text{C})$	=	60 A *
$Q_C$	=	194 nC *

#### Features

- Gen4 Thin Chip Technology for Low  $V_F$
- Superior Figure of Merit  $Q_C \cdot V_F$
- 100% Avalanche (UIL) Tested
- Enhanced Surge Current Withstand Capability
- Temperature Independent Fast Switching
- Low Thermal Resistance
- Positive Temperature Coefficient of  $V_F$
- High dV/dt Ruggedness

#### Package



T0-247-3

#### Advantages

- Improved System Efficiency
- High System Reliability
- Optimal Price Performance
- Reduced Cooling Requirements
- Increased System Power Density
- Zero Reverse Recovery Current
- Easy to Parallel without Thermal Runaway
- Enables Extremely Fast Switching

#### Applications

- Power Factor Correction (PFC)
- Electric Vehicles and Battery Chargers
- Solar Inverters
- High Frequency Converters
- Switched Mode Power Supply (SMPS)
- Motor Drives
- Anti-Parallel / Free-Wheeling Diode
- Induction Heating & Welding

#### Absolute Maximum Ratings (At $T_C = 25^\circ\text{C}$ Unless Otherwise Stated)

Parameter	Symbol	Conditions	Values	Unit	Note
Repetitive Peak Reverse Voltage (Per Leg)	$V_{RRM}$		1200	V	
Continuous Forward Current (Per Leg / Per Device)	$I_F$	$T_C = 100^\circ\text{C}, D = 1$	55 / 110	A	Fig. 4
		$T_C = 135^\circ\text{C}, D = 1$	38 / 76		
		$T_C = 148^\circ\text{C}, D = 1$	30 / 60		
Non-Repetitive Peak Forward Surge Current, Half Sine Wave (Per Leg)	$I_{F,SM}$	$T_C = 25^\circ\text{C}, t_P = 10 \text{ ms}$	240	A	
		$T_C = 150^\circ\text{C}, t_P = 10 \text{ ms}$	192		
Repetitive Peak Forward Surge Current, Half Sine Wave (Per Leg)	$I_{F,RM}$	$T_C = 25^\circ\text{C}, t_P = 10 \text{ ms}$	144	A	
		$T_C = 150^\circ\text{C}, t_P = 10 \text{ ms}$	100		
Non-Repetitive Peak Forward Surge Current (Per Leg)	$I_{F,MAX}$	$T_C = 25^\circ\text{C}, t_P = 10 \mu\text{s}$	1200	A	
$i^2t$ Value (Per Leg)	$\int i^2 dt$	$T_C = 25^\circ\text{C}, t_P = 10 \text{ ms}$	288	$\text{A}^2\text{s}$	
Non-Repetitive Avalanche Energy (Per Leg)	$E_{AS}$	$L = 0.6 \text{ mH}, I_{AS} = 30 \text{ A}$	271	mJ	
Diode Ruggedness (Per Leg)	dV/dt	$V_R = 0 \sim 960 \text{ V}$	200	V/ns	
Power Dissipation (Per Leg / Per Device)	$P_{TOT}$	$T_C = 25^\circ\text{C}$	313 / 626	W	Fig. 3
Operating and Storage Temperature	$T_j, T_{stg}$		-55 to 175	$^\circ\text{C}$	

\* Per Device

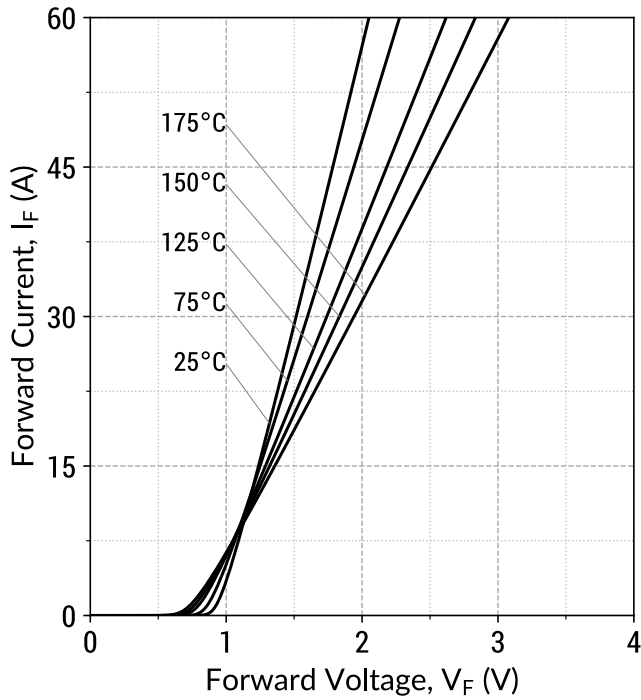
### Electrical Characteristics (Per Leg)

Parameter	Symbol	Conditions	Values			Unit	Note
			Min.	Typ.	Max.		
Diode Forward Voltage	$V_F$	$I_F = 30\text{ A}, T_j = 25^\circ\text{C}$		1.5	1.8	V	Fig. 1
		$I_F = 30\text{ A}, T_j = 175^\circ\text{C}$		1.9			
Reverse Current	$I_R$	$V_R = 1200\text{ V}, T_j = 25^\circ\text{C}$		2	20	$\mu\text{A}$	Fig. 2
		$V_R = 1200\text{ V}, T_j = 175^\circ\text{C}$		20			
Total Capacitive Charge	$Q_C$	$I_F \leq I_{F,MAX}$ $di_F/dt = 200\text{ A}/\mu\text{s}$	$V_R = 400\text{ V}$		67	nC	Fig. 7
			$V_R = 800\text{ V}$		97		
Switching Time	$t_s$		$V_R = 400\text{ V}$ $V_R = 800\text{ V}$	< 10		ns	
Total Capacitance	C	$V_R = 1\text{ V}, f = 1\text{ MHz}$		1101		pF	Fig. 6
		$V_R = 800\text{ V}, f = 1\text{ MHz}$		64			

### Thermal/Package Characteristics

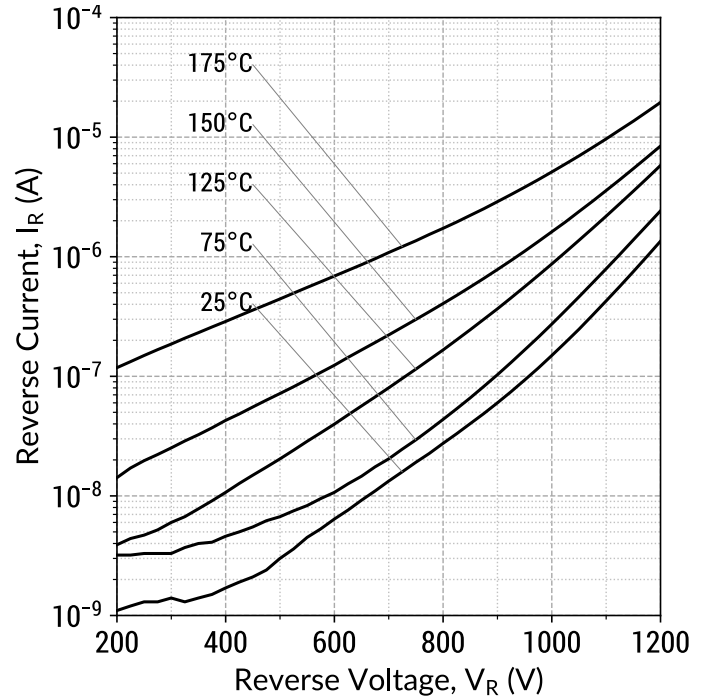
Parameter	Symbol	Conditions	Values			Unit	Note
			Min.	Typ.	Max.		
Thermal Resistance, Junction - Case (Per Leg)	$R_{thJC}$			0.48		$^\circ\text{C}/\text{W}$	Fig. 9
Weight	$W_T$			6.1		g	
Mounting Torque	$T_M$	Screws to Heatsink			1.1	Nm	

Figure 1: Typical Forward Characteristics (Per Leg)



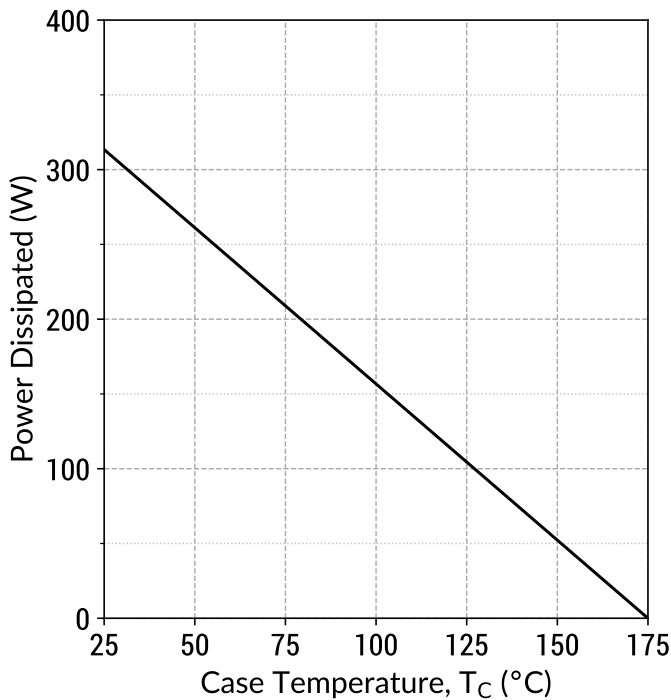
$$I_F = f(V_F, T_j); t_P = 250 \mu s$$

Figure 2: Typical Reverse Characteristics (Per Leg)



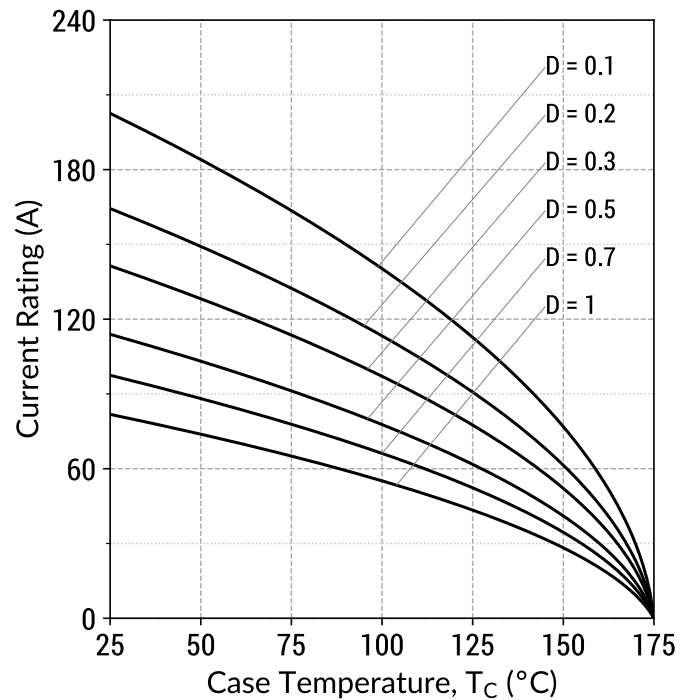
$$I_R = f(V_R, T_j)$$

Figure 3: Power Derating Curves (Per Leg)



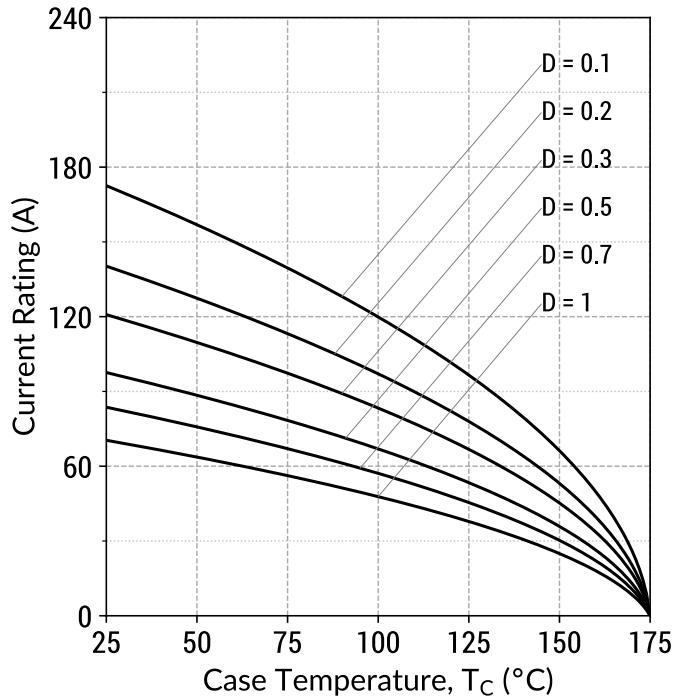
$$P_{TOT} = f(T_C); T_j = 175^\circ C$$

Figure 4: Current Derating Curves (Typical  $V_F$ ) (Per Leg)



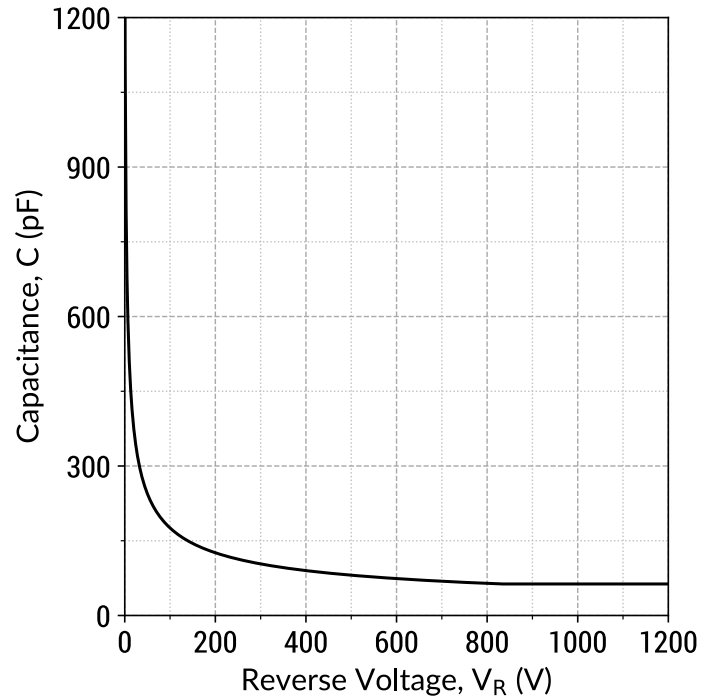
$$I_F = f(T_C); D = t_P/T; T_j \leq 175^\circ C; f_{sw} > 10kHz$$

Figure 5: Current Derating Curves (Maximum  $V_F$ ) (Per Leg)



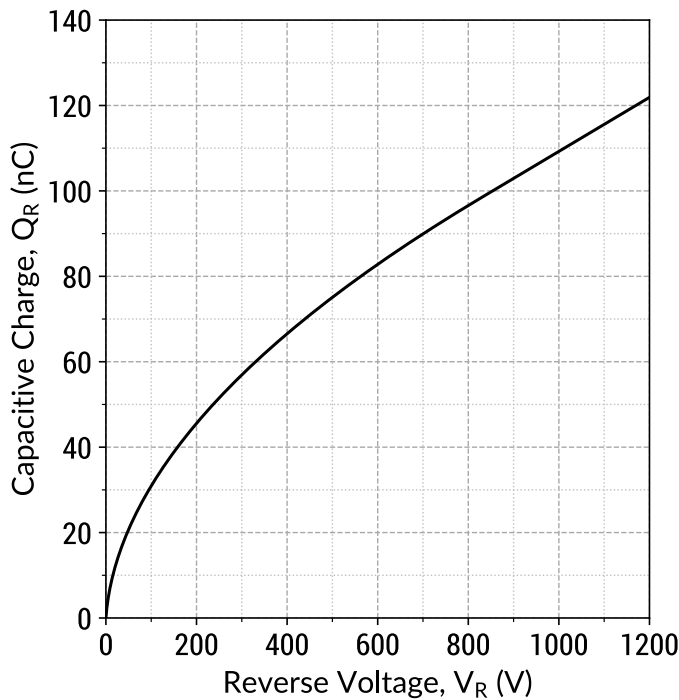
$I_F = f(T_C)$ ;  $D = t_P/T$ ;  $T_J \leq 175^\circ\text{C}$ ;  $f_{SW} > 10\text{kHz}$

Figure 6: Typical Junction Capacitance vs Reverse Voltage Characteristics (Per Leg)



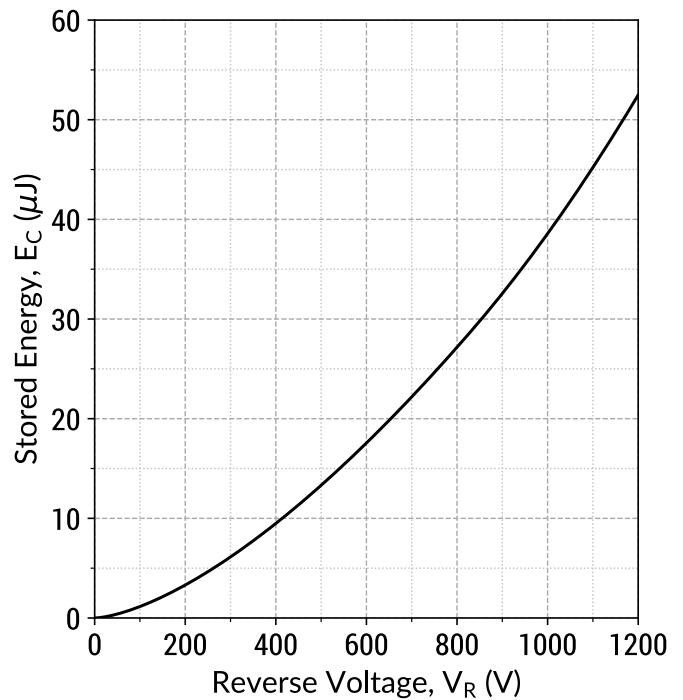
$C = f(V_R)$ ;  $f = 1\text{MHz}$

Figure 7: Typical Capacitive Charge vs Reverse Voltage Characteristics (Per Leg)



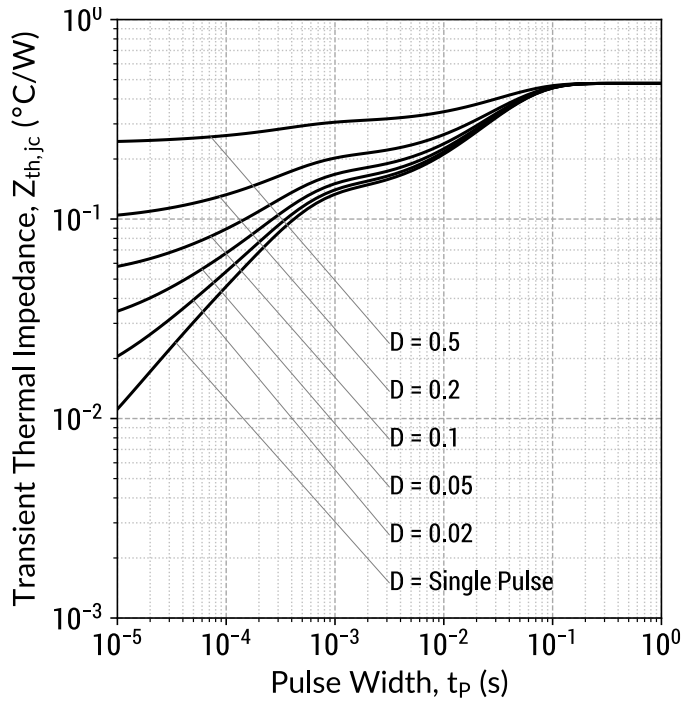
$Q_C = f(V_R)$ ;  $f = 1\text{MHz}$

Figure 8: Typical Capacitive Energy vs Reverse Voltage Characteristics (Per Leg)



$E_C = f(V_R)$ ;  $f = 1\text{MHz}$

Figure 9: Transient Thermal Impedance (Per Leg)



$$Z_{th,jc} = f(t_p, D); D = t_p/T$$

Figure 10: Forward Curve Model (Per Leg)



$$I_F = f(V_F, T_j)$$

**Forward Curve Model Equation:**

$$I_F = (V_F - V_{BI})/R_{DIFF} \text{ (A)}$$

**Built-In Voltage ( $V_{BI}$ ):**

$$V_{BI}(T_j) = m \times T_j + n \text{ (V)}$$

$$m = -0.00119 \text{ (V/°C)}$$

$$n = 1.01 \text{ (V)}$$

**Differential Resistance ( $R_{DIFF}$ ):**

$$R_{DIFF}(T_j) = a \times T_j^2 + b \times T_j + c \text{ (}\Omega\text{)}$$

$$a = 3.97e-07 \text{ (}\Omega\text{/°C}^2\text{)}$$

$$b = 5.5e-05 \text{ (}\Omega\text{/°C)}$$

$$c = 0.0163 \text{ (}\Omega\text{)}$$

**Forward Power Loss Equation:**

$$P_{LOSS} = V_{BI}(T_j) \times I_{AVG} + R_{DIFF}(T_j) \times I_{RMS}^2$$

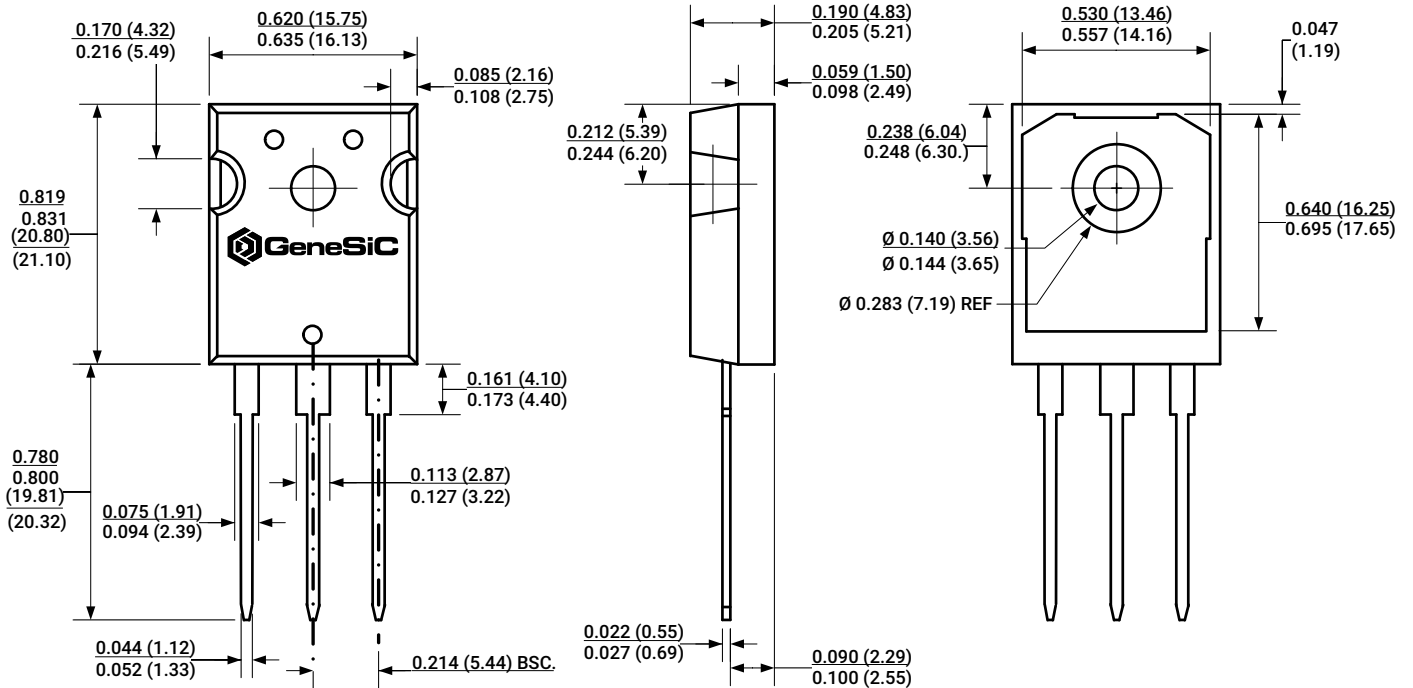
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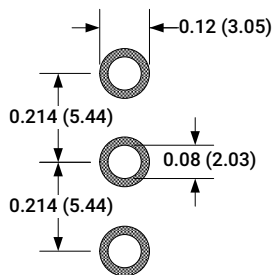


### Package Dimensions

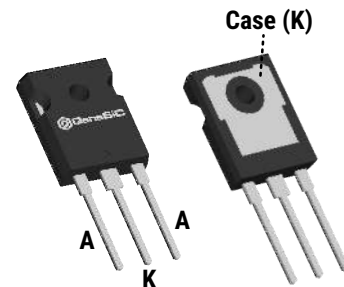
#### TO-247-3 Package Outline



#### Recommended Solder Pad Layout



#### Package View



#### NOTE

1. CONTROLLED DIMENSION IS INCH. DIMENSION IN BRACKET IS MILLIMETER.
2. DIMENSIONS DO NOT INCLUDE END FLASH, MOLD FLASH, MATERIAL PROTRUSIONS.

### Compliance

#### RoHS Compliance

The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS 2), as adopted by EU member states on January 2, 2013 and amended on March 31, 2015 by EU Directive 2015/863. RoHS Declarations for this product can be obtained from your GeneSiC representative.

#### REACH Compliance

REACH substances of high concern (SVHCs) information is available for this product. Since the European Chemical Agency (ECHA) has published notice of their intent to frequently revise the SVHC listing for the foreseeable future, please contact a GeneSiC representative to insure you get the most up-to-date REACH SVHC Declaration. REACH banned substance information (REACH Article 67) is also available upon request.

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### Related Links

- SPICE Models: [https://www.genesicsemi.com/sic-schottky-mps/GD2X30MPS12D/GD2X30MPS12D\\_SPICE.zip](https://www.genesicsemi.com/sic-schottky-mps/GD2X30MPS12D/GD2X30MPS12D_SPICE.zip)
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- Quality Manual: <https://www.genesicsemi.com/quality>

### Revision History

- Rev 21/Sep: Initial Release



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